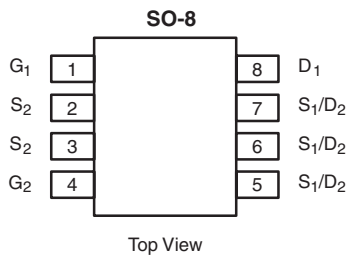


## Dual N-Channel 30-V (D-S) MOSFET with Schottky Diode

PRODUCT SUMMARY				
	V <sub>DS</sub> (V)	r <sub>DS(on)</sub> (Ω)	I <sub>D</sub> (A) <sup>a</sup>	Q <sub>g</sub> (Typ)
Channel-1	30	0.017 at V <sub>GS</sub> = 10 V	8.0	12.5
		0.0195 at V <sub>GS</sub> = 4.5 V	7.5	
Channel-2	30	0.010 at V <sub>GS</sub> = 10 V	15.2	17
		0.0115 at V <sub>GS</sub> = 4.5 V	14.1	

SCHOTTKY PRODUCT SUMMARY		
V <sub>DS</sub> (V)	V <sub>SD</sub> (V) Diode Forward Voltage	I <sub>F</sub> (A) <sup>a</sup>
30	0.43 V at 1.0 A	3.8



Ordering Information: Si4618DY-T1-E3 (Lead (Pb)-free)

### FEATURES

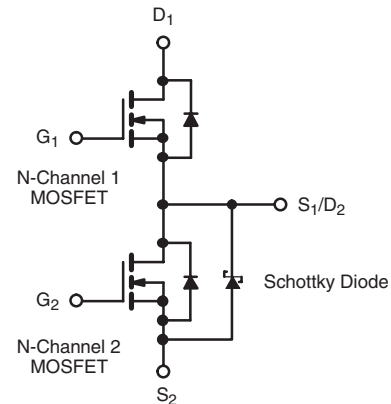
- TrenchFET<sup>®</sup> Power MOSFET
- 100 % R<sub>g</sub> and UIS Tested

### APPLICATIONS

- Notebook Logic DC-DC
- Low Current DC-DC



**RoHS**  
COMPLIANT



ABSOLUTE MAXIMUM RATINGS T <sub>A</sub> = 25 °C, unless otherwise noted				
Parameter	Symbol	Channel-1	Channel-2	Unit
Drain-Source Voltage	V <sub>DS</sub>	30	30	V
Gate-Source Voltage	V <sub>GS</sub>	± 16	± 16	
Continuous Drain Current (T <sub>J</sub> = 150 °C)	I <sub>D</sub>	T <sub>C</sub> = 25 °C	8.0	15.2
		T <sub>C</sub> = 70 °C	6.4	12.1
		T <sub>A</sub> = 25 °C	6.7 <sup>b, c</sup>	11.4 <sup>b, c</sup>
		T <sub>A</sub> = 70 °C	5.4 <sup>b, c</sup>	9.1 <sup>b, c</sup>
Pulsed Drain Current (10 μs Pulse Width)	I <sub>DM</sub>	35	60	A
Source-Drain Current Diode Current	I <sub>S</sub>	T <sub>C</sub> = 25 °C	1.8	
		T <sub>A</sub> = 25 °C	1.25 <sup>b, c</sup>	2.4 <sup>b, c</sup>
Pulsed Source-Drain Current	I <sub>SM</sub>	35	35	mJ
Single Pulse Avalanche Current	I <sub>AS</sub>	15	15	
Single Pulse Avalanche Energy	E <sub>AS</sub>	11.2	11.2	
Maximum Power Dissipation	P <sub>D</sub>	T <sub>C</sub> = 25 °C	1.98	4.16
		T <sub>C</sub> = 70 °C	1.26	2.66
		T <sub>A</sub> = 25 °C	1.38 <sup>b, c</sup>	2.35 <sup>b, c</sup>
		T <sub>A</sub> = 70 °C	0.88 <sup>b, c</sup>	1.5 <sup>b, c</sup>
Operating Junction and Storage Temperature Range	T <sub>J</sub> , T <sub>stg</sub>	- 55 to 150		°C

THERMAL RESISTANCE RATINGS							
Parameter	Symbol	Channel-1		Channel-2		Unit	
		Typ	Max	Typ	Max		
Maximum Junction-to-Ambient <sup>b, d</sup>	R <sub>thJA</sub>	72	90	43	53	°C/W	
Maximum Junction-to-Foot (Drain)	R <sub>thJF</sub>	51	63	25	30		

Notes:

- Based on T<sub>C</sub> = 25 °C.
- Surface Mounted on 1" x 1" FR4 Board.
- t = 10 sec.
- Maximum under Steady State conditions is 125 °C/W (Channel-1) and 100 °C/W (Channel-2).

<b>SPECIFICATIONS</b> $T_J = 25\text{ }^\circ\text{C}$ , unless otherwise noted							
Parameter	Symbol	Test Conditions		Min	Typ <sup>a</sup>	Max	Unit
<b>Static</b>							
Drain-Source Breakdown Voltage	$V_{DS}$	$V_{GS} = 0\text{ V}, I_D = 1\text{ mA}$	Ch-1	30			V
		$V_{GS} = 0\text{ V}, I_D = 1\text{ mA}$	Ch-2	30			
$V_{DS}$ Temperature Coefficient	$\Delta V_{DS}/T_J$	$I_D = 250\text{ }\mu\text{A}$	Ch-1		35		
$V_{GS(th)}$ Temperature Coefficient	$\Delta V_{GS(th)}/T_J$	$I_D = 250\text{ }\mu\text{A}$	Ch-1		-6		
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 1\text{ mA}$	Ch-1	1		2.5	
		$V_{DS} = V_{GS}, I_D = 1\text{ mA}$	Ch-2	1		2.5	
Gate-Body Leakage	$I_{GSS}$	$V_{DS} = 0\text{ V}, V_{GS} = \pm 16\text{ V}$	Ch-1			100	$\mu\text{A}$
		$V_{DS} = 0\text{ V}, V_{GS} = \pm 16\text{ V}$	Ch-2			100	
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = 30\text{ V}, V_{GS} = 0\text{ V}$	Ch-1			0.001	mA
		$V_{DS} = 30\text{ V}, V_{GS} = 0\text{ V}$	Ch-2		0.05	0.5	
		$V_{DS} = 30\text{ V}, V_{GS} = 0\text{ V}, T_J = 100\text{ }^\circ\text{C}$	Ch-1			0.025	
		$V_{DS} = 30\text{ V}, V_{GS} = 0\text{ V}, T_J = 100\text{ }^\circ\text{C}$	Ch-2		3	15	
On-State Drain Current <sup>b</sup>	$I_{D(on)}$	$V_{DS} = 5\text{ V}, V_{GS} = 10\text{ V}$	Ch-1	20			A
		$V_{DS} = 5\text{ V}, V_{GS} = 10\text{ V}$	Ch-2	20			
Drain-Source On-State Resistance <sup>b</sup>	$r_{DS(on)}$	$V_{GS} = 10\text{ V}, I_D = 8\text{ A}$	Ch-1		0.014	0.017	$\Omega$
		$V_{GS} = 10\text{ V}, I_D = 8\text{ A}$	Ch-2		0.0083	0.010	
		$V_{GS} = 4.5\text{ V}, I_D = 5\text{ A}$	Ch-1		0.016	0.0195	
		$V_{GS} = 4.5\text{ V}, I_D = 5\text{ A}$	Ch-2		0.0095	0.0115	
Forward Transconductance <sup>b</sup>	$g_{fs}$	$V_{DS} = 15\text{ V}, I_D = 8\text{ A}$	Ch-1		40		S
		$V_{DS} = 15\text{ V}, I_D = 8\text{ A}$	Ch-2		47		
<b>Dynamic<sup>a</sup></b>							
Input Capacitance	$C_{iss}$	Channel-1 $V_{DS} = 15\text{ V}, V_{GS} = 0\text{ V}, f = 1\text{ MHz}$	Ch-1		1535		pF
Output Capacitance	$C_{oss}$		Ch-2		2290		
Reverse Transfer Capacitance	$C_{rss}$	Channel-2 $V_{DS} = 15\text{ V}, V_{GS} = 0\text{ V}, f = 1\text{ MHz}$	Ch-1		205		
			Ch-2		360		
Total Gate Charge	$Q_g$	$V_{DS} = 15\text{ V}, V_{GS} = 10\text{ V}, I_D = 8\text{ A}$	Ch-1		29	44	nC
		$V_{DS} = 15\text{ V}, V_{GS} = 10\text{ V}, I_D = 8\text{ A}$	Ch-2		39	59	
		Channel-1 $V_{DS} = 15\text{ V}, V_{GS} = 4.5\text{ V}, I_D = 8\text{ A}$	Ch-1		12.5	19	
			Ch-2		17	26	
Gate-Source Charge	$Q_{gs}$	Channel-2 $V_{DS} = 15\text{ V}, V_{GS} = 4.5\text{ V}, I_D = 8\text{ A}$	Ch-1		4.1		
Gate-Drain Charge	$Q_{gd}$		Ch-2		5.6		
Gate Resistance	$R_g$	$f = 1\text{ MHz}$	Ch-1		1.8	3.0	$\Omega$
			Ch-2		1.9	3.0	



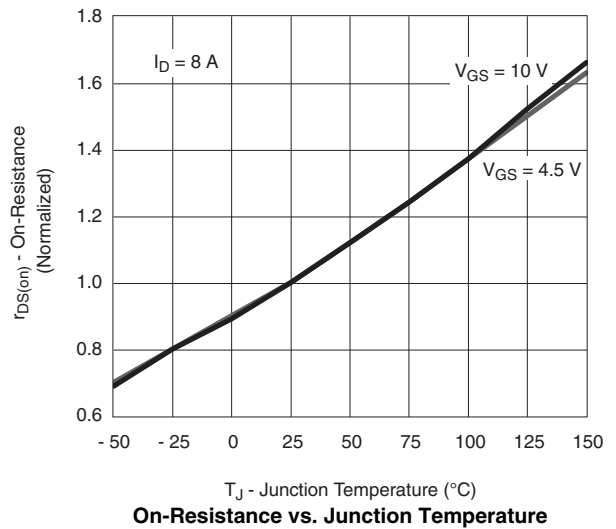
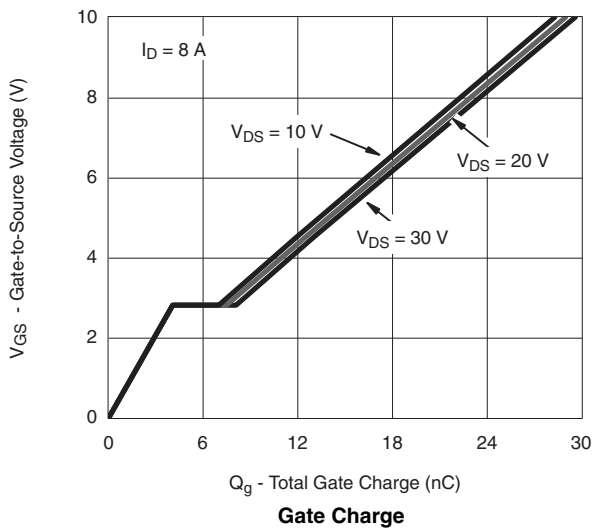
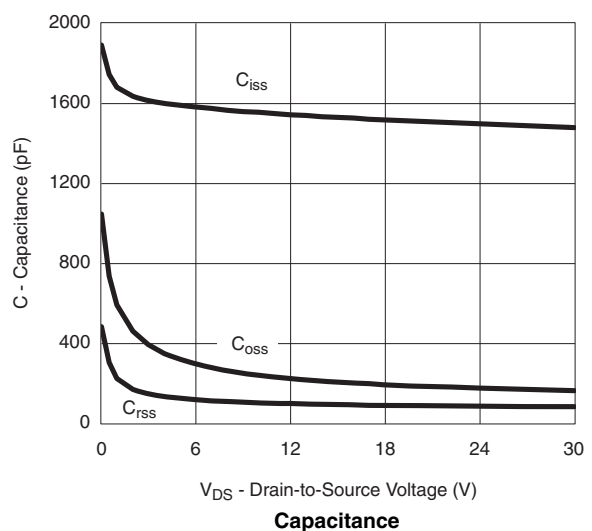
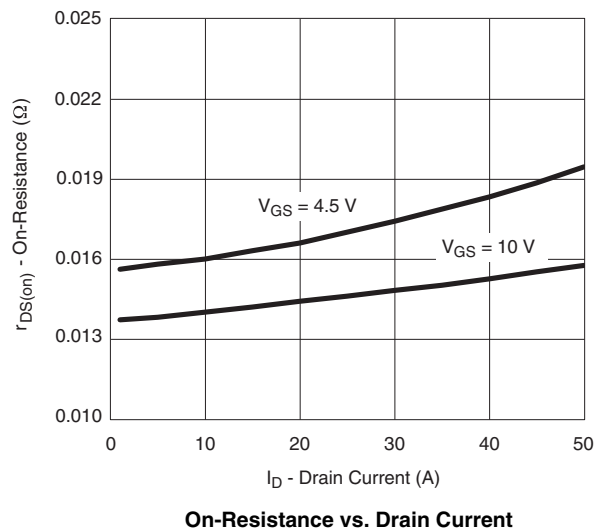
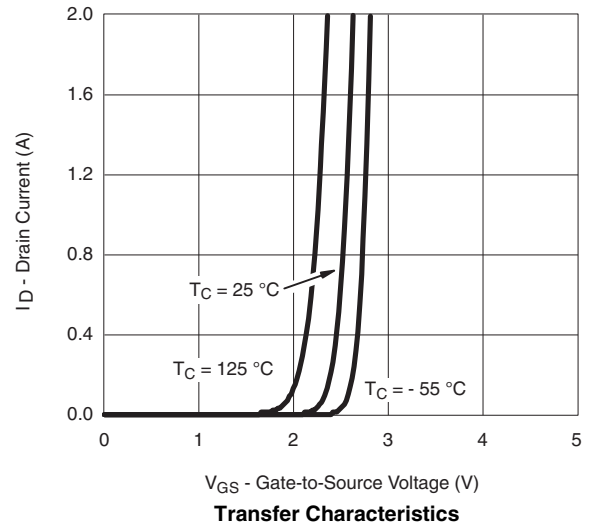
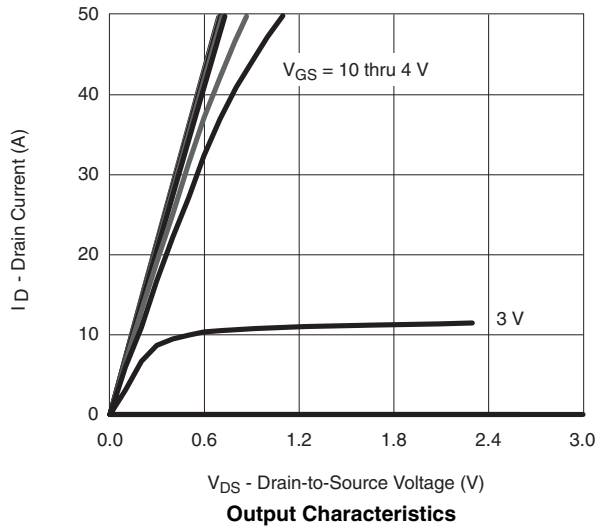
<b>SPECIFICATIONS</b> $T_J = 25\text{ }^\circ\text{C}$ , unless otherwise noted							
Parameter	Symbol	Test Conditions	Min	Typ <sup>a</sup>	Max	Unit	
<b>Dynamic<sup>a</sup></b>							
Turn-On Delay Time	$t_{d(on)}$	Channel-1 $V_{DD} = 15\text{ V}, R_L = 3\ \Omega$ $I_D \cong 5\text{ A}, V_{GEN} = 10\text{ V}, R_g = 1\ \Omega$  Channel-2 $V_{DD} = 15\text{ V}, R_L = 3\ \Omega$ $I_D \cong 5\text{ A}, V_{GEN} = 10\text{ V}, R_g = 1\ \Omega$  Channel-1 $V_{DD} = 15\text{ V}, R_L = 3\ \Omega$ $I_D \cong 5\text{ A}, V_{GEN} = 4.5\text{ V}, R_g = 1\ \Omega$  Channel-2 $V_{DD} = 15\text{ V}, R_L = 3\ \Omega$ $I_D \cong 5\text{ A}, V_{GEN} = 4.5\text{ V}, R_g = 1\ \Omega$	Ch-1		8	15	ns
			Ch-2		9	16	
Rise Time	$t_r$		Ch-1		22	33	
			Ch-2		24	36	
Turn-Off Delay Time	$t_{d(off)}$		Ch-1		20	30	
			Ch-2		26	39	
Fall Time	$t_f$		Ch-1		8	15	
			Ch-2		8	15	
Turn-On Delay Time	$t_{d(on)}$	Ch-1		24	36		
		Ch-2		24	36		
Rise Time	$t_r$	Ch-1		87	130		
		Ch-2		97	145		
Turn-Off Delay Time	$t_{d(off)}$	Ch-1		30	45		
		Ch-2		35	53		
Fall Time	$t_f$	Ch-1		34	51		
		Ch-2		45	68		
<b>Drain-Source Body Diode Characteristics</b>							
Continuous Source-Drain Diode Current	$I_S$	$T_C = 25\text{ }^\circ\text{C}$	Ch-1			1.8	A
			Ch-2			3.8	
Pulse Diode Forward Current <sup>a</sup>	$I_{SM}$		Ch-1			35	
			Ch-2			35	
Body Diode Voltage	$V_{SD}$	$I_S = 2\text{ A}$ $I_S = 1\text{ A}$	Ch-1		0.77	1.1	V
			Ch-2		0.37	0.43	
Body Diode Reverse Recovery Time	$t_{rr}$	Channel-1 $I_F = 4\text{ A}, di/dt = 100\text{ A}/\mu\text{s}, T_J = 25\text{ }^\circ\text{C}$  Channel-2 $I_F = 4\text{ A}, di/dt = 100\text{ A}/\mu\text{s}, T_J = 25\text{ }^\circ\text{C}$	Ch-1		22	33	ns
			Ch-2		26	39	
Body Diode Reverse Recovery Charge	$Q_{rr}$		Ch-1		15	23	nC
			Ch-2		15	23	
Reverse Recovery Fall Time	$t_a$		Ch-1		13		ns
			Ch-2		13		
Reverse Recovery Rise Time	$t_b$		Ch-1		9		
			Ch-2		13		

Notes:

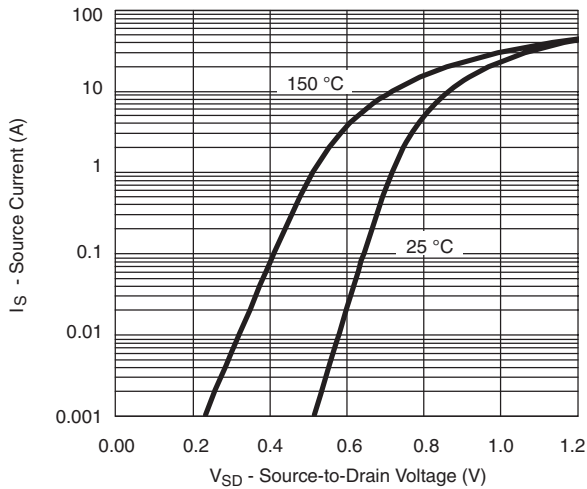
- a. Guaranteed by design, not subject to production testing.
- b. Pulse test; pulse width  $\leq 300\ \mu\text{s}$ , duty cycle  $\leq 2\%$ .

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

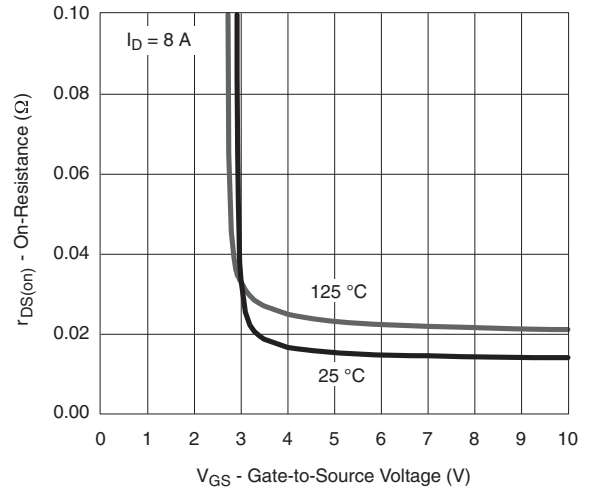
## CHANNEL-1 TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



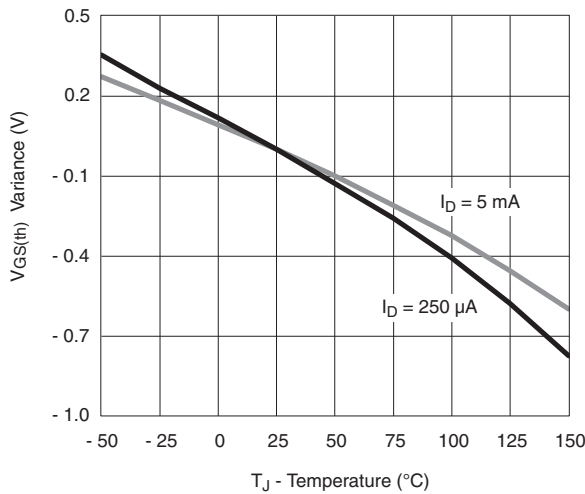
## CHANNEL-1 TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



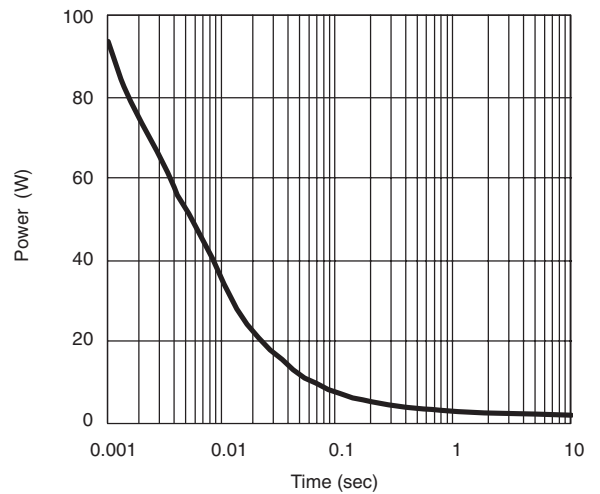
Source-Drain Diode Forward Voltage



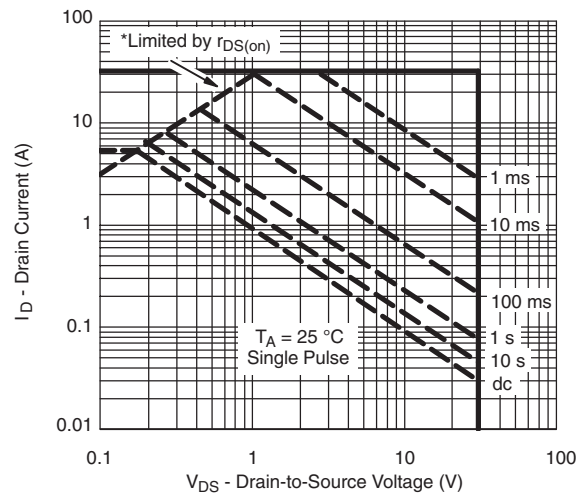
On-Resistance vs. Gate-to-Source Voltage



Threshold Voltage



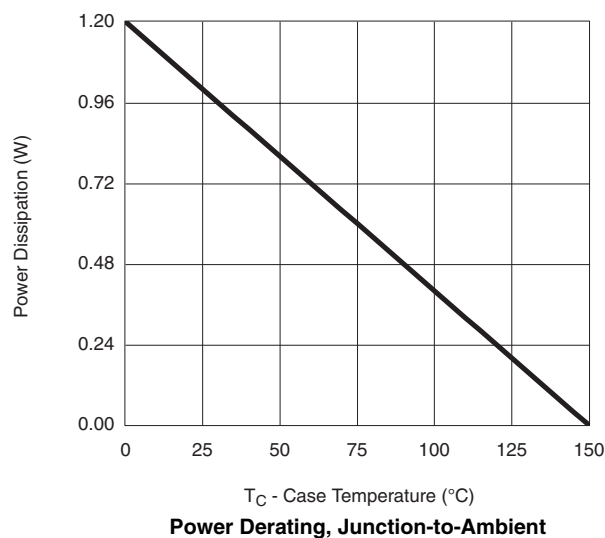
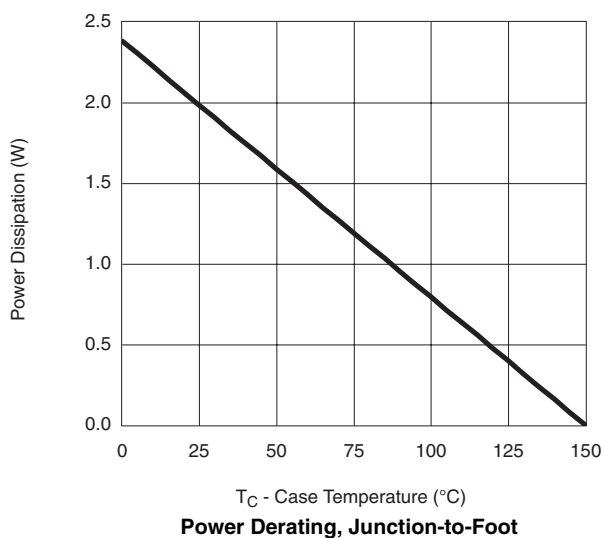
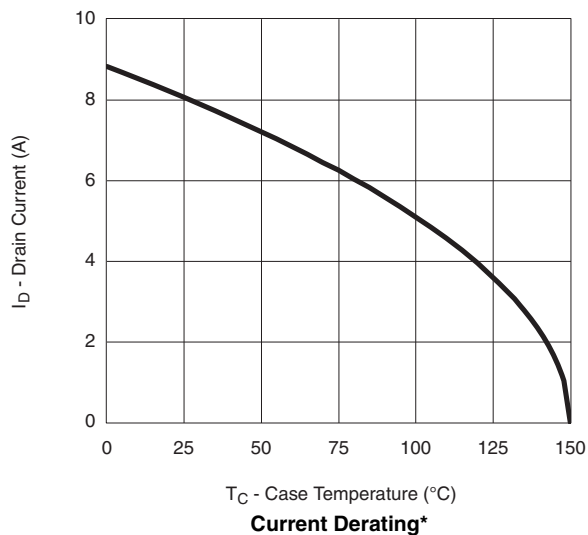
Single Pulse Power, Junction-to-Ambient



\* $V_{GS} >$  minimum  $V_{GS}$  at which  $r_{DS(on)}$  is specified

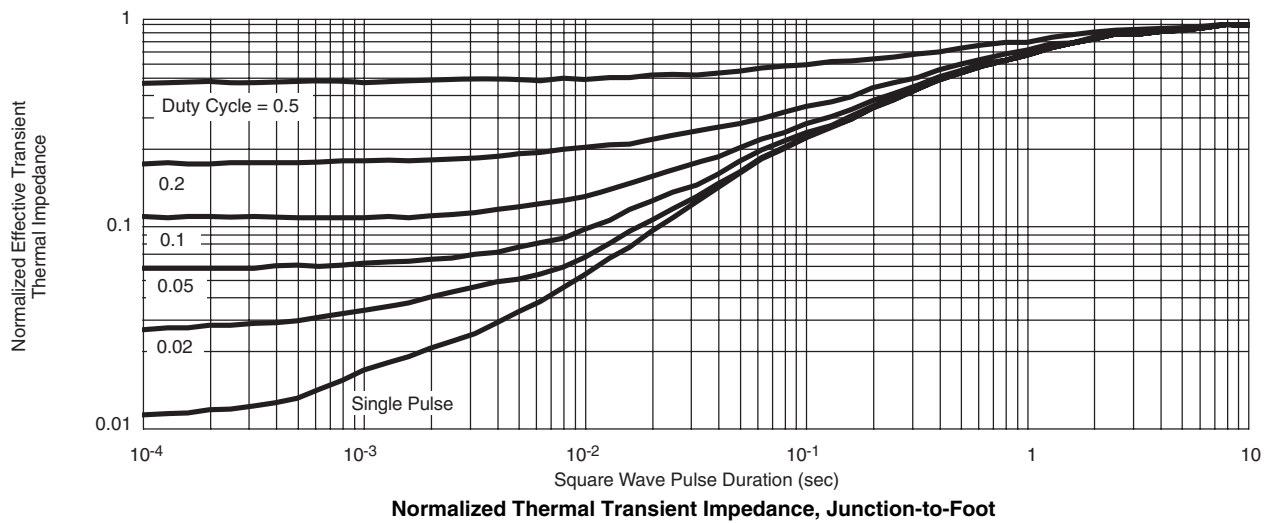
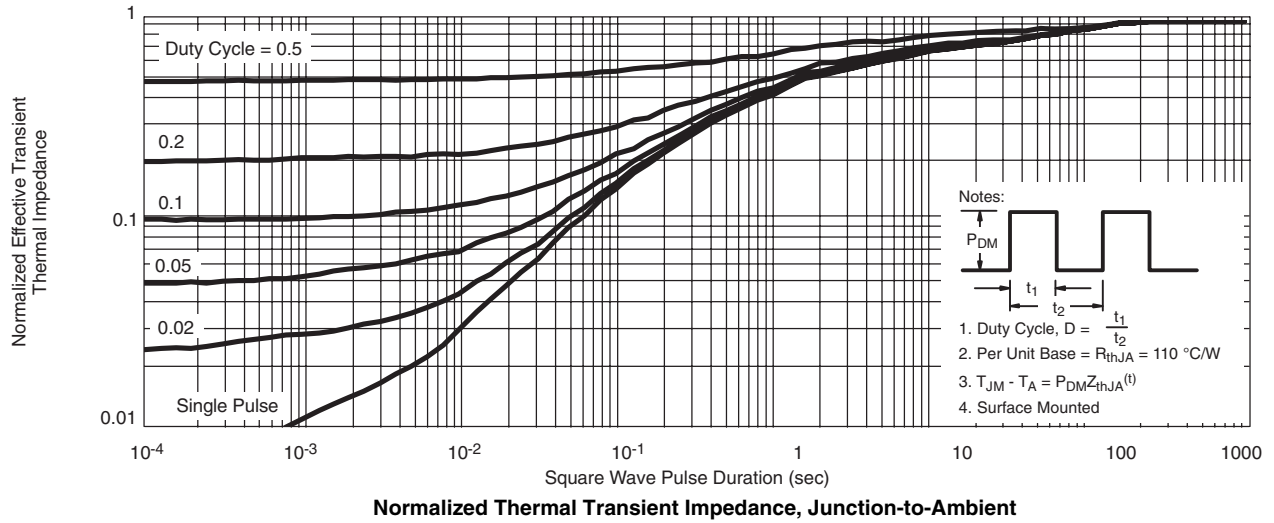
Safe Operating Area, Junction-to-Ambient

## CHANNEL-1 TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

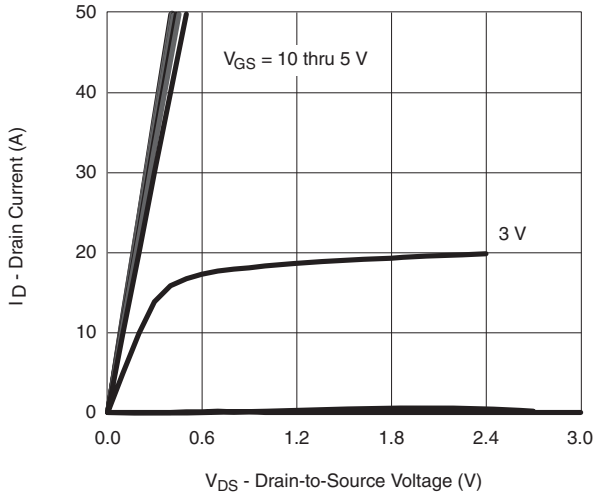


\*The power dissipation  $P_D$  is based on  $T_{J(max)} = 150$  °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

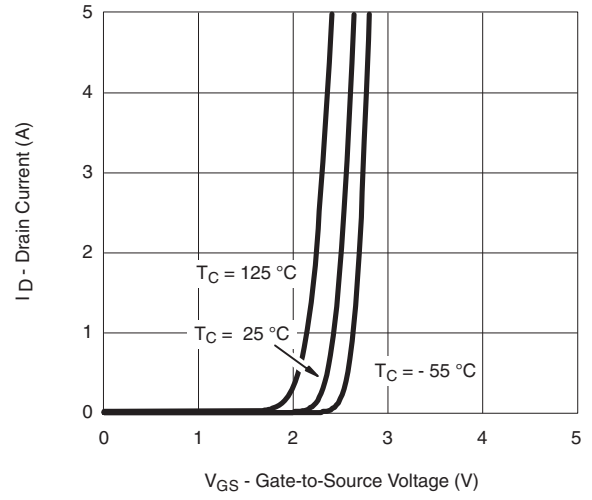
**CHANNEL-1 TYPICAL CHARACTERISTICS** 25 °C, unless otherwise noted



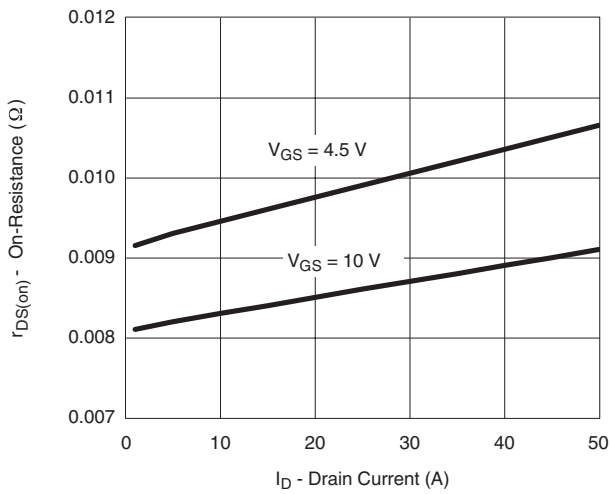
## CHANNEL-2 TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



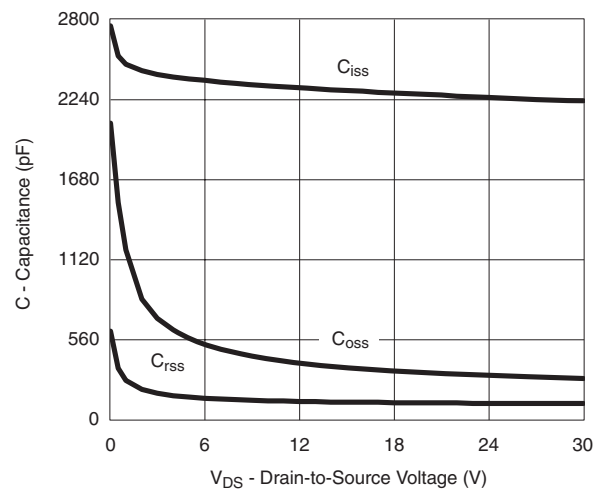
**Output Characteristics**



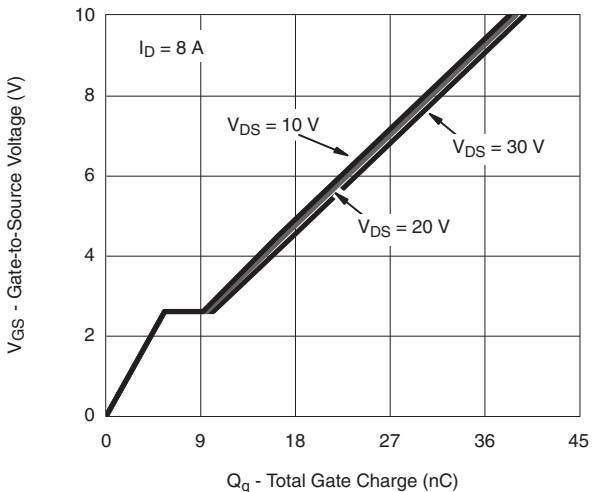
**Transfer Characteristics**



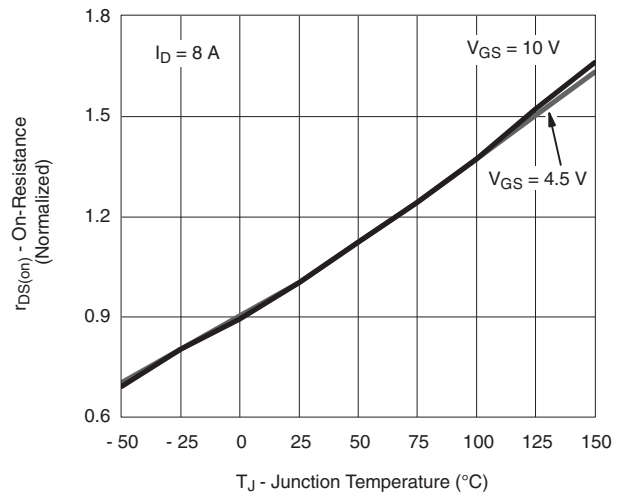
**On-Resistance vs. Drain Current**



**Capacitance**



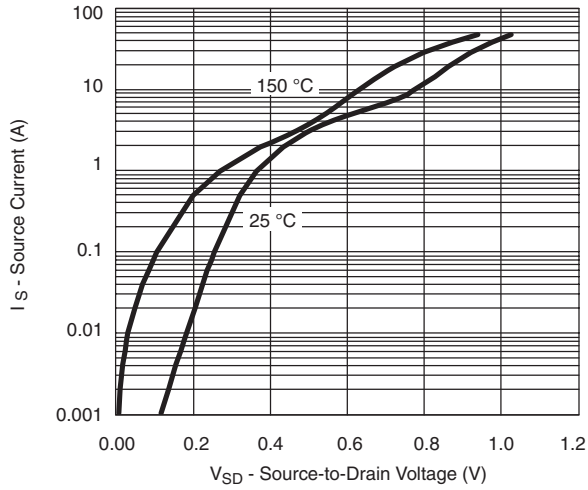
**Gate Charge**



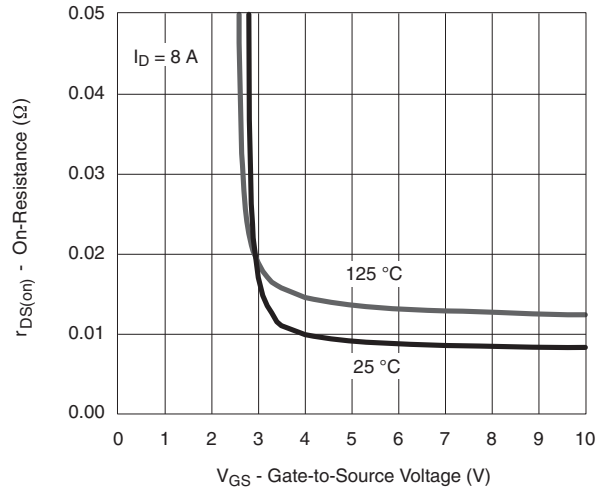
**On-Resistance vs. Junction Temperature**



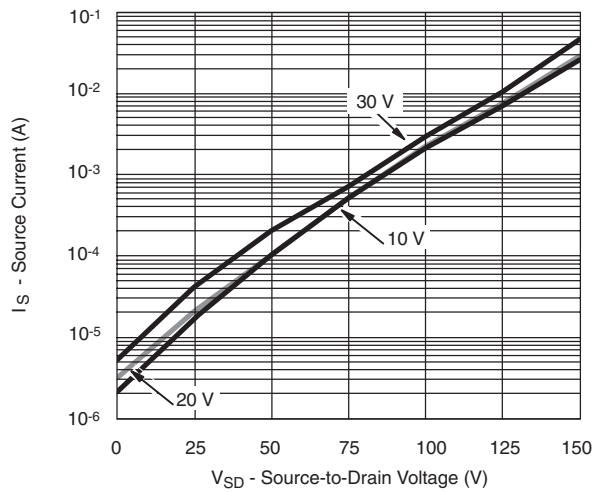
## CHANNEL-2 TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



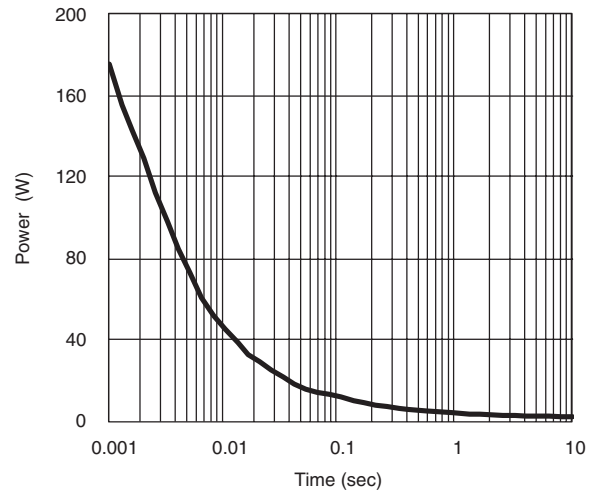
**Source-Drain Diode Forward Voltage**



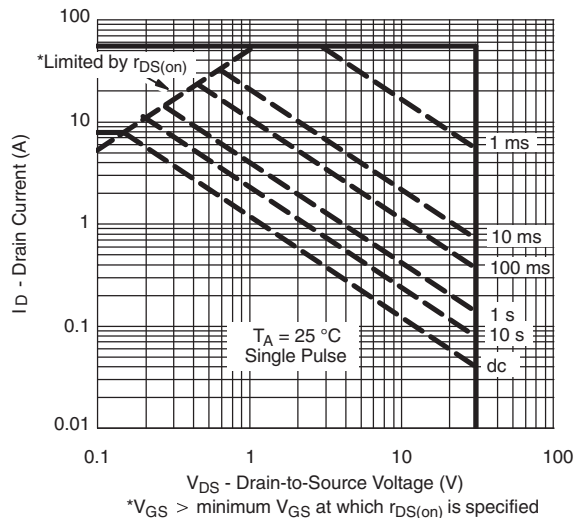
**On-Resistance vs. Gate-to-Source Voltage**



**Reverse Current (Schottky)**

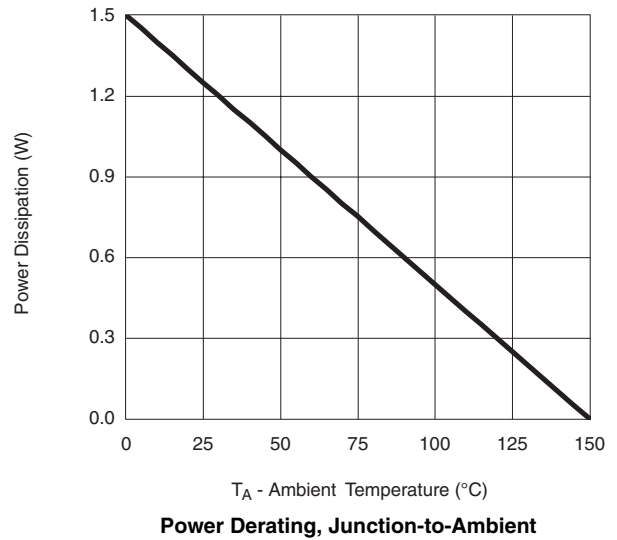
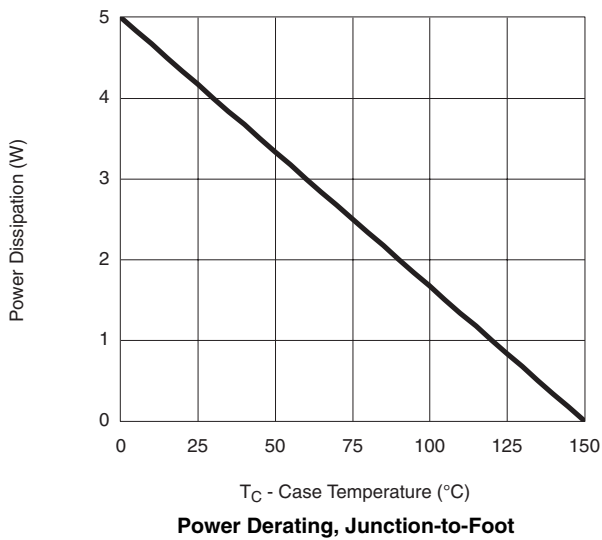
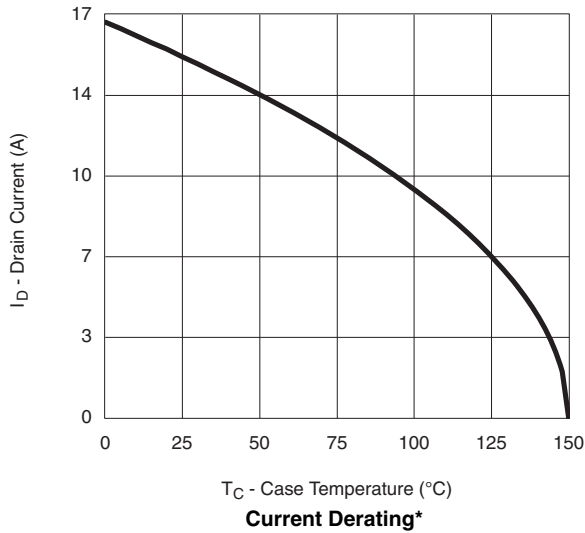


**Single Pulse Power, Junction-to-Ambient**



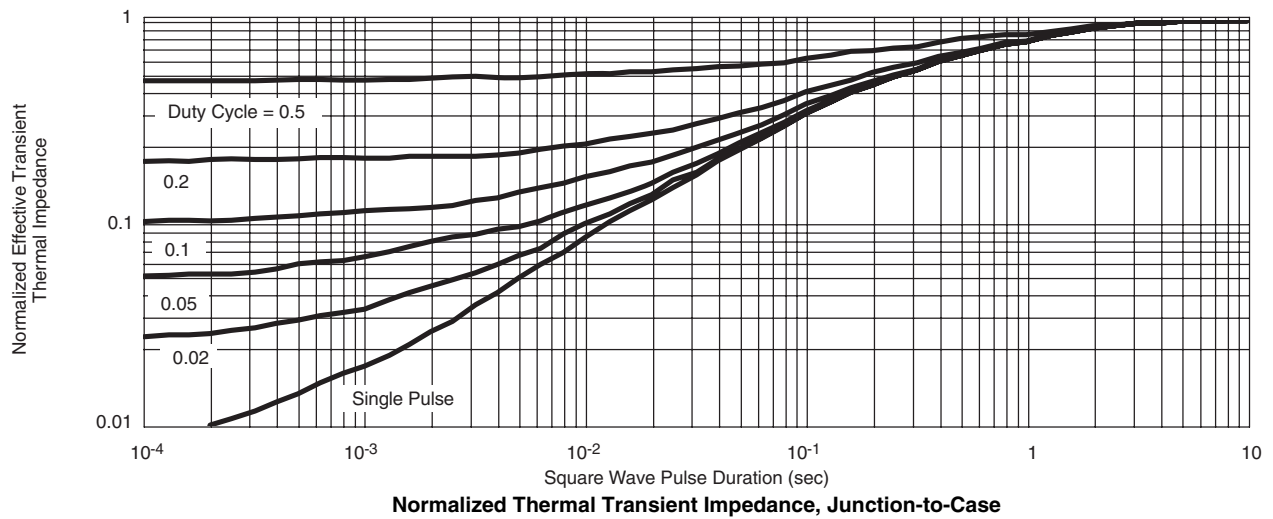
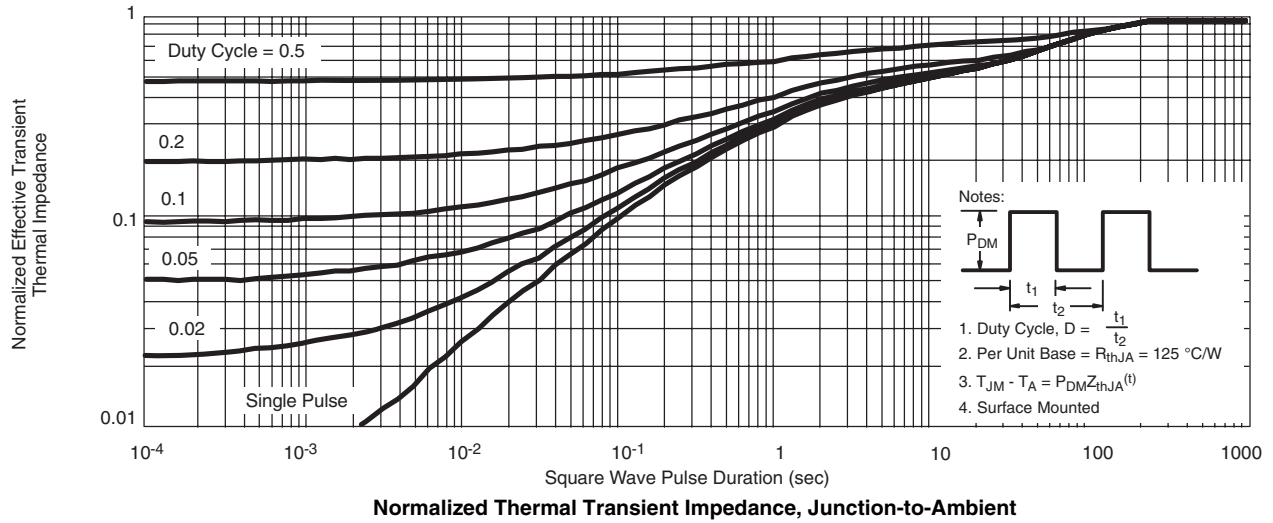
**Safe Operating Area, Junction-to-Ambient**

**CHANNEL-2 TYPICAL CHARACTERISTICS** 25 °C, unless otherwise noted



\*The power dissipation  $P_D$  is based on  $T_{J(max)} = 150$  °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

**CHANNEL-2 TYPICAL CHARACTERISTICS** 25 °C, unless otherwise noted



Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see <http://www.vishay.com/ppg?74450>.



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